

PNP Silicon

FEATURE

We declare that the material of product compliance with RoHS requirements.

Pb-Free package is available

RoHS product for packing code suffix "G"

Halogen free product for packing code suffix "H"

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
8550PLT1	85P	3000/Tape&Reel
8550QLT1	1YD	3000/Tape&Reel
8550RLT1	1YF	3000/Tape&Reel



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	V
Collector-Base voltage	V_{CBO}	40	V
Emitter-base Voltage	V_{EBO}	5	V
Collector current-continuoun	I_C	800	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board (1) $T_A = 25\text{ }^\circ\text{C}$	P_D	225	mW
Derate above $25\text{ }^\circ\text{C}$		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25\text{ }^\circ\text{C}$	P_D	300	mW
Derate above $25\text{ }^\circ\text{C}$		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICEMARKING

8550QLT1 = 1YD 8550PLT1 = 85P

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

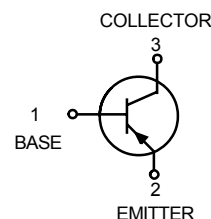
Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 1.0\text{mA}$)	$V_{(BR)CEO}$	25	—	—	V
Emitter-Base Breakdown Voltage ($I_E = 100\mu\text{A}$)	$V_{(BR)EBO}$	5	—	—	V
Collector-Base Breakdown voltage ($I_C = 100\mu\text{A}$)	$V_{(BR)CBO}$	40	—	—	V
Collector Cutoff Current ($V_{CB} = 35\text{V}$)	I_{CBO}	—	—	150	nA
Emitter Cutoff Current ($V_{EB} = 4\text{V}$)	I_{EBO}	—	—	150	nA

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

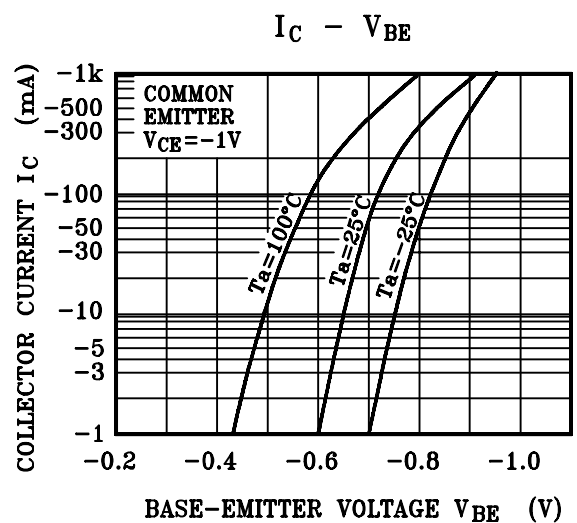
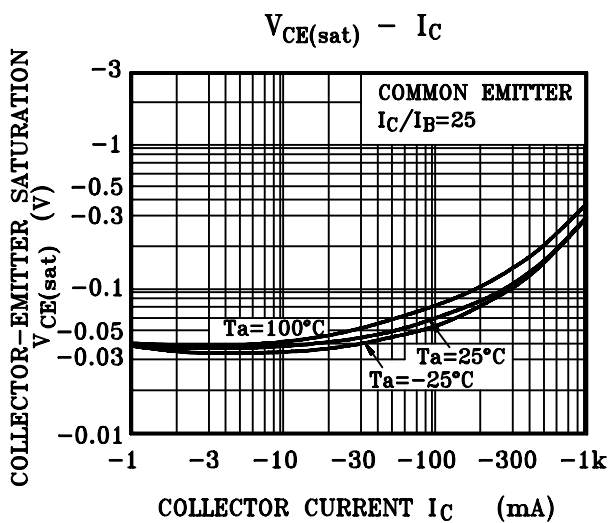
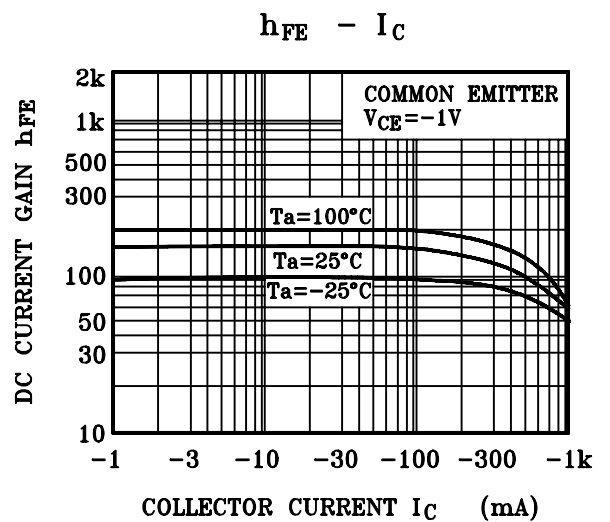
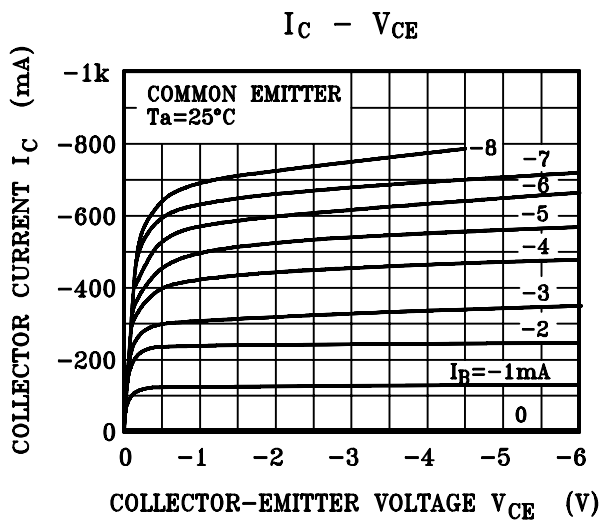


ON CHARACTERISTICS

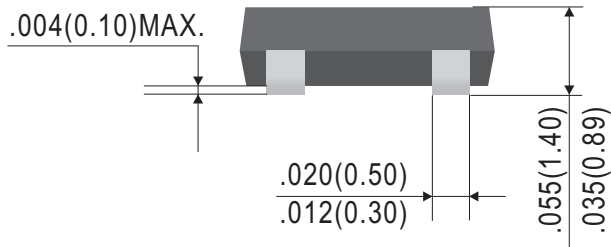
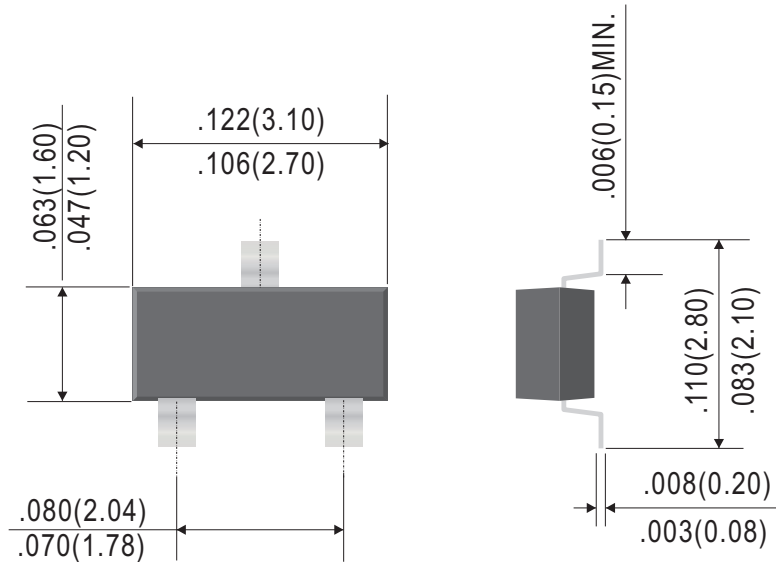
Characteristic	Symbol	Min	Typ	Max	Unit
DC Current Gain ($I_C = 100\text{mA}$ $V_{CE} = 1\text{V}$)	h_{FE}	100	—	100	
Collector-Emitter Saturation Voltage ($I_C = 800\text{mA}$ $I_B = 80\text{mA}$)	$V_{CE(S)}$	—	—	0.5	V

NOTE:

*	P	Q	R
h_{FE}	100~200	150~300	200~400



SOT-23



Dimensions in inches and (millimeters)

